



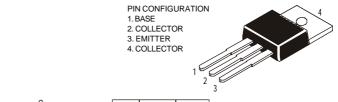


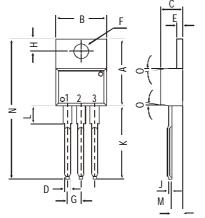
## **TO-220 Plastic Package**

BDX53, BDX53A, BDX53B, BDX53C BDX54, BDX54A, BDX54B, BDX54C

BDX53, 53A, 53B, 53C NPN PLASTIC POWER TRANSISTORS BDX54, 54A, 54B, 54C PNP PLASTIC POWER TRANSISTORS

Power Darlingtons for Linear and Switching Applications





DIM	MIN.	MAX.	
Α	14.42	16.51	
В	9.63	10.67	
С	3.56	4.83	
D		0.90	
Ε	1.15	1.40	
F	3.75	3.88	
G	2.29	2.79	
Н	2.54	3.43	
J		0.56	
K	12.70	14.73	
L	2.80	4.07	
М	2.03	2.92	
N		31.24	
0	DEG 7		
	A B C D E F G H J K L	A 14.42 B 9.63 C 3.56 D E 1.15 F 3.75 G 2.29 H 2.54 J K 12.70 L 2.80 M 2.03 N	

## ABSOLUTE MAXIMUM RATINGS

		53 54		53B 54B		
Collector-base voltage (open emitter)	$V_{CBO}$	max. 45	60	<i>80</i>	100	V
Collector-emitter voltage (open base)	$V_{CEO}$	max. 45	60	<i>80</i>	100	V
Collector current	$I_C$	max.	8.0			$\boldsymbol{A}$
Total power dissipation up to $T_C = 25^{\circ}C$	$P_{tot}$	max.	(	30		W
Junction temperature	$T_{j}$	max.	1	<i>50</i>		${}^{\!$
Collector-emitter saturation voltage	J					
$I_C = 3 A; I_B = 12 mA$	$V_{CEsat}$	max.	2	2.0		V
D.C. current gain						
$I_C = 3 A; \ V_{CE} = 3 \ V$	$h_{FE}$	min.	7	50		
DATINICE (at T. 95°C and a sthematic and Gard)						

**RATINGS** (at  $T_A$ =25°C unless otherwise specified) Limiting values

Liming values		<i>J J</i>	JJH	JJD	JJC	
		<b>54</b>	54A	54B	<b>54C</b>	
Collector-base voltage (open emitter)	$V_{CBO}$	max. 45	<i>60</i>	<i>80</i>	100	V
Collector-emitter voltage (open base)	$V_{C\!E\!O}$	max. 45	<i>60</i>	<i>80</i>	100	V
Emitter-base voltage (open collector)	$V_{EBO}$	max.	5.	.0		V

# BDX53, BDX53A, BDX53B, BDX53C BDX54, BDX54A, BDX54B, BDX54C

Collector current Collector current (Peak value) Base current Total power dissipation upto T <sub>C</sub> =25°C Derate above 25°C Junction temperature Storage temperature	$I_{C}$ $I_{CM}$ $I_{B}$ $P_{tot}$ $T_{j}$ $T_{Stg}$	max. max. max. max. max. max.	1 0. 6 0. 13	0 2 2 0 48 50 5 to +	150	$egin{array}{c} A & & & & & & & & & & & & & & & & & & $
•	1 SIG		-00	ιυ τ	150	C
THERMAL RESISTANCE	D		0	00		ooti.
From junction to case	$R_{thj-c}$		2.08 7.0			°CW °CW
From junction to ambient	$R_{th j-a}$		7.	U		CW
CHARACTERISTICS						
$T_{amb} = 25$ °C unless otherwise specified						
		<i>53</i>	53A		53C	
C.H. to C. C.		<b>54</b>	54A	54B	<i>54C</i>	
Collector cutoff current	T	mar. 0.2				A
$I_B = 0; V_{CB} = 45 V$	$I_{CBO}$	max. 0.2	0.2	_	_	mA
$I_B = 0; V_{CB} = 60 \text{ V}$	$I_{CBO}$	max	<i>0.2</i> –	-	_	mA
$I_B = 0$ ; $V_{CB} = 80 \text{ V}$	$I_{CBO}$	max	_	0.2	0.2	mA mA
$I_B = 0; \ V_{CB} = 100 \ V$ $I_B = 0; \ V_{CE} = 22 \ V$	I <sub>CBO</sub> I <sub>CEO</sub>	max. – max. 0.5	_	_	<i>0.2</i> –	mA
IB = 0, $VCE = 22$ $VIB = 0$ ; $VCE = 30$ $V$		max	0.5	_	_	mA
$I_{B} = 0$ , $V_{CE} = 30 \text{ V}$ $I_{B} = 0$ ; $V_{CE} = 40 \text{ V}$	I <sub>CEO</sub> I <sub>CEO</sub>	max. –	<i>0.5</i>	0.5	_	mA
$I_B = 0$ ; $V_{CE} = 40 \text{ V}$ $I_B = 0$ ; $V_{CE} = 50 \text{ V}$	ICEO ICEO	max. –		0.5	0.5	mA
Emitter cut-off current	ICEO	max. –			0.5	шл
$I_C = 0; V_{EB} = 5 V$	$I_{EBO}$	max.	2	0		mA
Breakdown voltages	¹EBU	max.	~.	U		1112 1
$I_C = 100 \text{ mA}; I_B = 0$	V <sub>CEO(sus)</sub>	* min 45	60	80	100	V
$I_C = 1 \text{ mA}; I_E = 0$	$V_{CBO}$	min. 45	60	80	100	$\stackrel{\cdot}{V}$
$I_F = 1 \text{ mA}; I_C = 0$	$V_{EBO}$	min.	5.			V
Saturation voltages	LDO					
$I_C = 3 A$ ; $I_B = 12 \text{ mA}$	$V_{CEsat}^*$	max.	2.	0		V
2	$V_{BEsat}^*$	max.	2.	5		V
D.C. current gain						
$I_C = 3 A$ ; $V_{CE} = 3 V$	$h_{\!F\!E}^*$	min.	73	50		
Small signal current gain						
$I_C = 3 A; V_{CE} = 4 V; f = 1.0 MHz$	$/h_{f\!e}/$	min.	4.	0		
Output capacitance $f = 1.0 \text{ MHz}$						
$I_E = 0; V_{CB} = 10 V$ <b>NPN</b>	$C_{o}$	max.		00		pF
PNP	$C_{o}$	max.	20	00		pF
Parallel-diode forward voltage	17			~		<b>T</b> 7
$I_F = 3 A$	$V_F$	max.		5		V
$I_F = 8 A$	$V_F$	typ.	2.	Э		V

<sup>\*</sup> Pulse test: pulse width  $\leq$  300  $\mu$ s; duty cycle  $\leq$  2%

#### **Notes**

### **Disclaimer**

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